2SB936

Preliminary

PNP EPITAXIAL SILICON TRANSISTOR

SILICON PNP EPITAXIAL PLANAR TYPE

DESCRIPTION

The UTC **2SB936** is a silicon PNP epitaxial planar type, it uses UTC's advanced technology to provide the customers with high DC current gain, low collector to emitter saturation voltage and high switch speed, etc.

The UTC **2SB936** is suitable for small electronic equipment and printed circuit board, etc.

1 TO-252

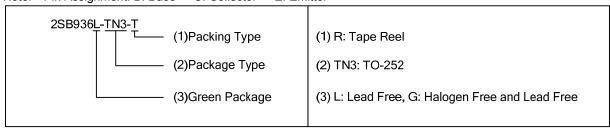
■ FEATURES

- * High DC current gain
- * Low collector to emitter saturation voltage
- * High switch speed

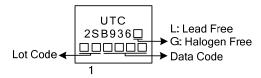
■ ORDERING INFORMATION

	Ordering Number		Deskore	Pin Assignment			Deakins
	Lead Free	Halogen Free	Package	1	2	3	Packing
Ī	2SB936L-TN3-R	2SB936G-TN3-R	TO-252	В	С	Е	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I _C	-10	Α
Peak Collector Current	I _{CP}	-20	Α
Collector Power Dissipation	Pc	40	W
T _A =25°C		1.3	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 ~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-10mA, I _E =0	-40			V
Collector-Emitter Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-20			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _C =-10mA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-40V, I _E =0			-50	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-50	μΑ
DC Current Gain	h _{FE1}	V _{CE} =-2V, I _C =-0.1A	45			
DC Current Gain	h _{FE2}	V_{CE} =-2V, I_{C} =-3 A	90			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-10A, I _B =-0.33A			-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I _C =-10A, I _B =-0.33A			-1.5	V
Transition Frequency	f _T	V _{CE} =-10V, f=10MHz, I _C =-0.5A		100		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz, I _E =0		400		pF
Turn-On Time	t _{on}			0.1		μs
Storage Time	ts	I _C =-3A, I _{B1} =-0.1A, I _{B2} =0.1A		0.5		μs
Fall Time	t _r			0.1		μs

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